

# MRF16006



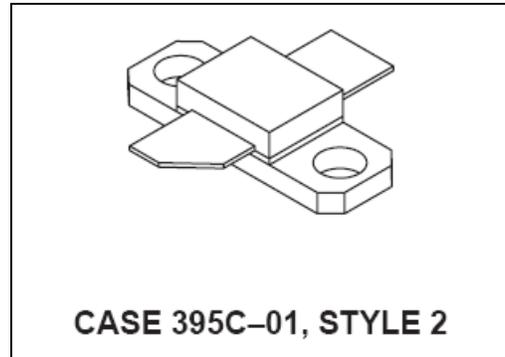
The RF Line NPN Silicon Power Transistor  
6.0W , 1.6GHz, 28V

M/A-COM Products  
Released - Rev. 07.07

## Product Image

Designed for 28 V microwave large-signal, common base, Class C, CW amplifier applications in the range 1600 – 1640 MHz.

- Specified 28 V, 1.6 GHz Class C characteristics
  - Output power = 6 W
  - Minimum gain = 7.4 dB, @ 6 W
  - Minimum efficiency = 40% @ 6 W
- Characterized with series equivalent large-signal parameters from 1500 MHz to 1700 MHz
- Silicon nitride passivated
- Gold metalized, emitter ballasted for long life and resistance to metal migration



## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CES</sub>	60	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Collector-Current	I <sub>C</sub>	1.0	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	26 0.15	Watts W/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

## THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case (1) (2)	R <sub>θJC</sub>	6.8	°C/W
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(1) Thermal measurement performed using CW RF operating condition.

(2) Thermal resistance is determined under specified RF operating conditions by infrared measurement techniques.

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**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**OFF CHARACTERISTICS**

Collector–Emitter Breakdown Voltage ( $I_C = 40\text{ mAdc}$ , $V_{BE} = 0$ )	$V_{(BR)CES}$	55	—	—	Vdc
Collector–Base Breakdown Voltage ( $I_C = 40\text{ mAdc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	55	—	—	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 2.5\text{ mAdc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ( $V_{CE} = 28\text{ Vdc}$ , $V_{BE} = 0$ )	$I_{CES}$	—	—	2.5	mAdc

**ON CHARACTERISTICS**

DC Current Gain ( $I_{CE} = 0.2\text{ Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	$h_{FE}$	20	—	80	—
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**DYNAMIC CHARACTERISTICS**

Output Capacitance ( $V_{CB} = 28\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$C_{ob}$	11	—	—	pf
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**FUNCTIONAL TESTS**

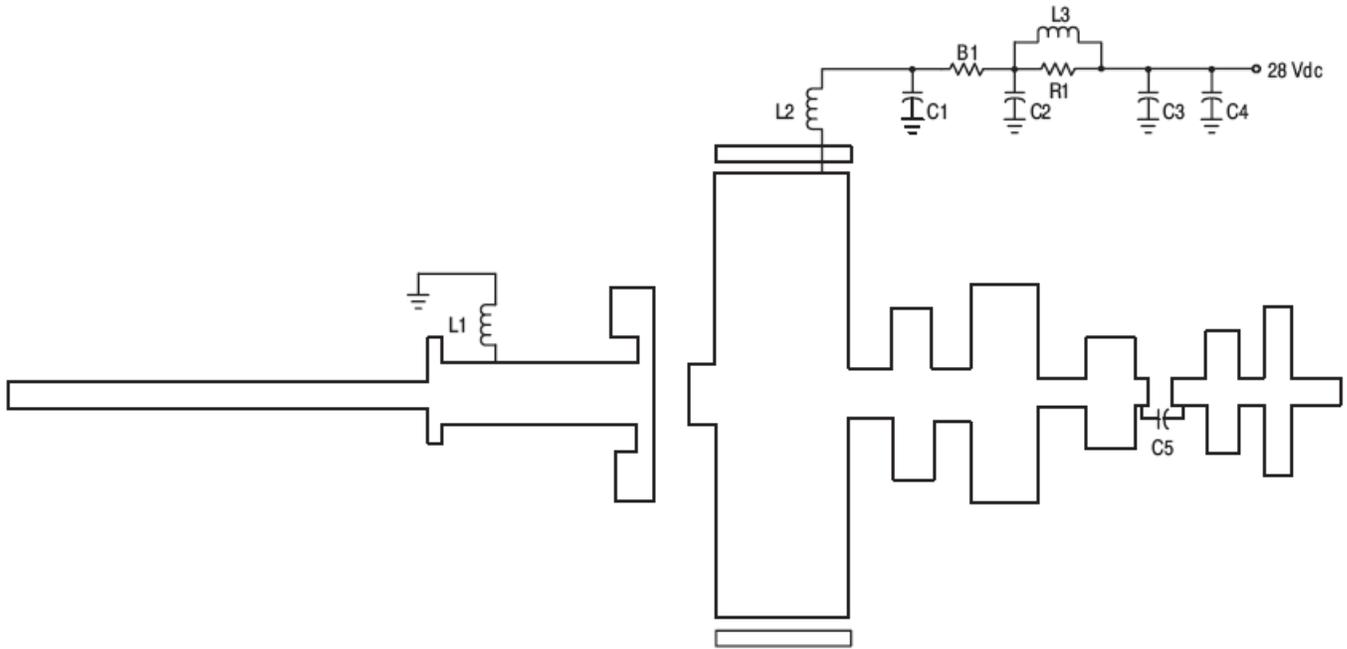
Common–Base Amplifier Power Gain ( $V_{CC} = 28\text{ Vdc}$ , $P_{out} = 6\text{ Watts}$ , $f = 1600/1640\text{ MHz}$ )	$G_{pe}$	7.4	—	—	dB
Collector Efficiency ( $V_{CC} = 28\text{ Vdc}$ , $P_{out} = 6\text{ Watts}$ , $f = 1600/1640\text{ MHz}$ )	$\eta$	40	45	—	%
Return Loss ( $V_{CC} = 28\text{ Vdc}$ , $P_{out} = 6\text{ Watts}$ , $f = 1600/1640\text{ MHz}$ )	$I_{RL}$	—	8.0	—	dB
Output Mismatch Stress ( $V_{CC} = 28\text{ Vdc}$ , $P_{out} = 6\text{ Watts}$ , $f = 1600\text{ MHz}$ , Load VSWR = 3:1 all phase angles at frequency of test)	$\psi$	No Degradation in Output Power			

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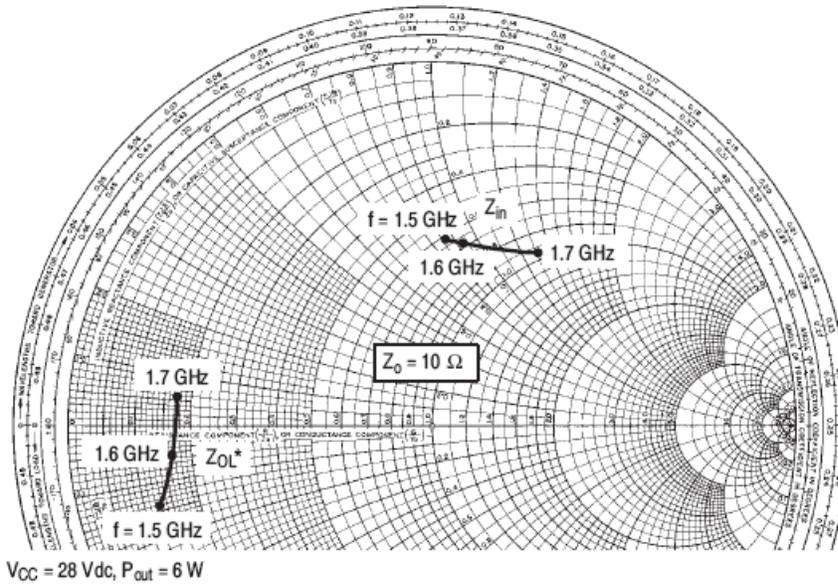
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Board Material – Teflon<sup>®</sup> Glass Laminate Dielectric  
Thickness – 0.30",  $\epsilon_r = 2.55$ ", 2.0 oz. Copper

B1	Fair Rite Bead on #24 Wire	C4	47 $\mu$ F, 50 V, Electrolytic Cap
C1, C5	100 pF, B Case, ATC Chip Cap	L1, L2	3 Turns, #18, 0.133" ID, 0.15" Long
C2	0.1 $\mu$ F, Dipped Mica Cap	L3	9 Turns, #24 Enamel
C3	0.1 $\mu$ F, Chip Cap	R1	82 $\Omega$ , 1.0 W, Carbon Resistor

Figure 1. MRF16006 Test Fixture Schematic



f MHz	Z <sub>in</sub> Ohms	Z <sub>OL</sub> * Ohms
1500	6.28 + j 8.53	1.22 - j 1.37
1600	7.04 + j 9.00	1.58 - j 0.53
1700	9.55 + j 12.86	1.71 + j 0.39

Z<sub>OL</sub>\* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 2. Series Equivalent Input/Output Impedance

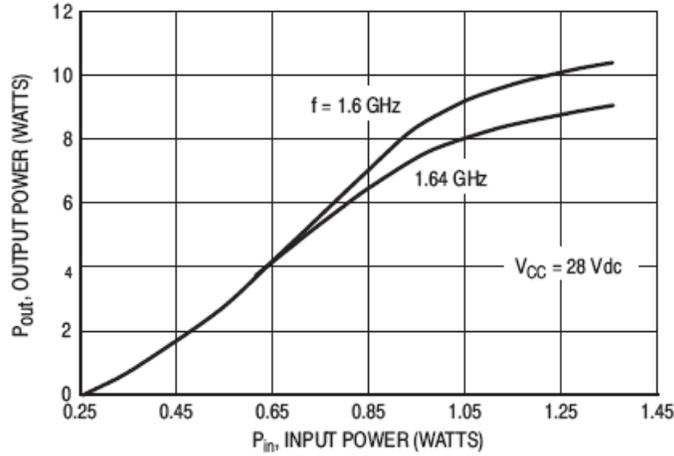


Figure 3. Output Power versus Input Power

## PACKAGE DIMENSIONS

